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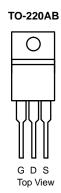
N-Channel 100 V (D-S) 175 °C MOSFET

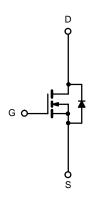
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
100	0.005 at V _{GS} = 10 V	110 ^a		

FEATURES

- DT-Trench Power MOSFET
- New Package with Low Thermal Resistance
- 100 % R_g Tested







N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	ST _C = 25 °C, unless o	therwise noted		
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage		V _{GS} ± 20		7 v
Continuous Proin Current (T = 175 °C)	T _C = 25 °C		110 ^a	
Continuous Drain Current (T _J = 175 °C)	T _C = 125 °C	I _D	87 ^a	A
Pulsed Drain Current		I _{DM}	510	
Avalanche Current		I _{AR}	75	
Repetitive Avalanche Energy ^b	L = 0.5 mH	E _{AR}	680	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	D	375 ^c	W
waximum rowei bissipation	T _A = 25 °C	P _D	3.75	7
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Limit	Unit	
Junction-to-Ambient	PCB Mount (TO-263) ^d	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	C/VV	

Notes:

- a. Package limited.
- b. Duty cycle ≤ 1 %.
- c. See SOA curve for voltage derating.
 d. When mounted on 1" square PCB (FR-4 material).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	100				
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 80 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
		V _{GS} = 10 V, I _D = 30 A		0.005	0.006		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.017	Ω	
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C			0.025		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	25			S	
Dynamic ^b	•			•			
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz		6700		pF	
Output Capacitance	C _{oss}			750			
Reverse Transfer Capacitance	C _{rss}			280			
Total Gate Charge ^c	Qg			110	160	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 85 \text{ A}$		24			
Gate-Drain Charge ^c	Q _{gd}			24			
Gate Resistance	R _g		1.0		6.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			20	30		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_1 = 0.6 \Omega$		125	200	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 85 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		55	85		
Fall Time ^c	t _f			130	195		
Source-Drain Diode Ratings and Cha	aracteristics 7	C _C = 25 °C ^b	'				
Continuous Current	I _S				110	_	
Pulsed Current	I _{SM}				510	Α	
Forward Voltage ^a	V _{SD}	I _F = 85 A, V _{GS} = 0 V		1.0	1.5	V	
Reverse Recovery Time	t _{rr}			70	140	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 50 A, dl/dt = 100 A/μs		5.5	10	Α	
Reverse Recovery Charge	Q _{rr}	-		0.19	0.35	μC	

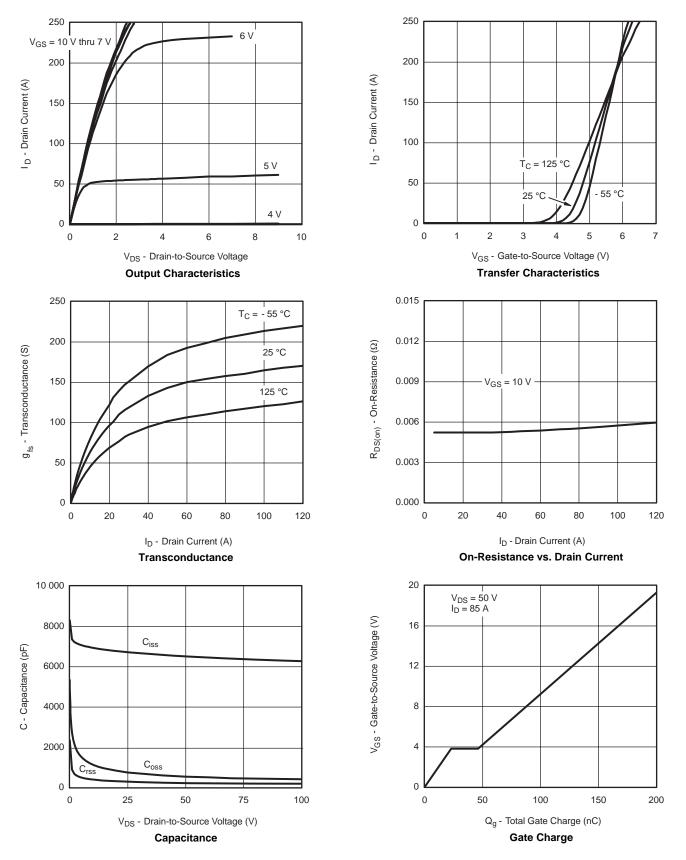
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

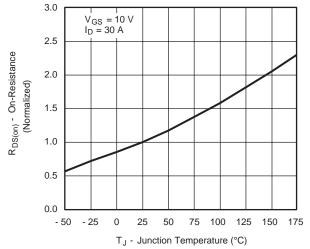


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

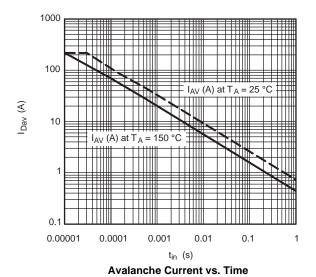




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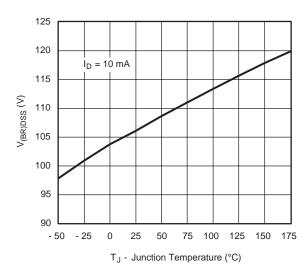


On-Resistance vs. Junction Temperature



100 Is - Source Current (A) T_J = 150 °C $T_J = 25$ °C 10 0 0.3 0.6 0.9 1.2 V_{SD} - Source-to-Drain Voltage (V)

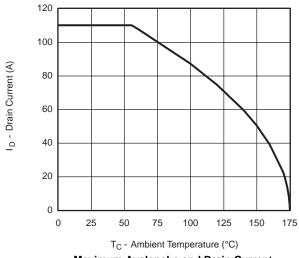
Source-Drain Diode Forward Voltage



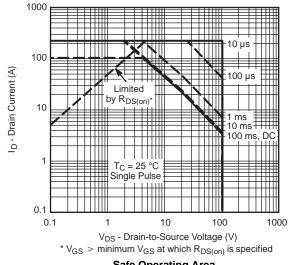
Drain Source Breakdown vs. Junction Temperature



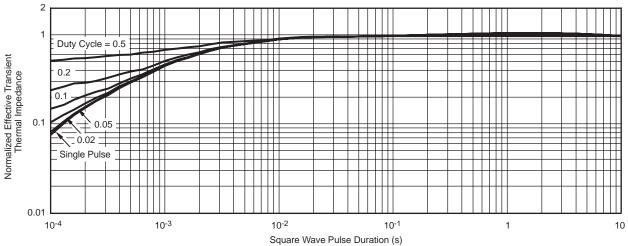
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature







Normalized Thermal Transient Impedance, Junction-to-Case





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